

D. Thin Film Process Technology **분과**

Room F
창의관 (B114)

일 시 : 2월 17일(금) 09:30-11:00

세션명 : [FF1-D] Device and Characterization Technology

좌 장 : 최리노(인하대학교), 전상훈(삼성종합기술원)

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- FF1-D-1 09:30-10:00 **[Invited]** Gate-Last Process Integration Issues with High-k Gate Dielectric and Metal Gate (HKMG) Technology
저자: Changhwan Choi
소속: Division of Materials Science and Engineering, Hanyang University
- FF1-D-2 10:00-10:15 **Scaling of Equivalent Oxide Thickness and Modulation of Effective Work Function using Transition Metal (La,Ti) – Inserted TiN Metal Gate on HfO₂**
저자: Hyo Kyeom Kim¹, Hyung-Suk Jung¹, Sang Young Lee¹, Il-Hyuk Yu¹, Tae Joo Park², and Cheol Seong Hwang¹
소속: ¹WCU Hybrid Materials Program, Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University, ²Department of Materials Engineering, Hanyang University
- FF1-D-3 10:15-10:30 **Application of Charge Pumping Method into Extracting Trap Distribution in Polysilicon Thin Film Transistors**
저자: Cuong Nguyen Manh¹, Tae-Young Jang¹, Dong-Hyoub Kim¹, Jungwoo Kim¹, Jun Suk Chang¹, Musarrat Hasan¹, Hoichang Yang¹, Jae Kyeong Jeong¹, Bio Kim², Jae-young Ahn², Kihyun Hwang², and Rino Choi¹
소속: ¹Inha University, ²Process Development P/J2, Semiconductor R&D Center, Samsung Electronics Co., Ltd.
- FF1-D-4 10:30-10:45 **Capacitance-voltage Measurement of Leaky Al₂O₃ MIM Capacitor using Time Domain Reflectometry (TDR)**
저자: 김용훈¹, 이영곤¹, 김진주², 정육진¹, 송승철³, 이병훈^{1,2}
소속: ¹광주과학기술원 신소재공학부, ²광주과학기술원 나노바이오재료 전자공학과, ³Texas Instruments Inc.

- FF1-D-5 10:45-11:00 **Effects of W Diffusion Barrier on Inhibition of AlN Formation in Ti/Al based Ohmic Contacts on N-polar N-GaN**
저자: Yang Hee Song, Jun Ho Son, Buem Joon, and Jong-Lam Lee
소속: 포항공과대학교 신소재공학과 첨단재료과학부